

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Daisuke KOMADA, et al.**

Group Art Unit: 1756

Serial No.: **10/058,426**

Examiner: **BARRECA, Nicole M.**

Filed: **January 30, 2002**

Confirmation No.: **4298**

For: **METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING SILICON CARBIDE FILM**

Attorney Docket No.: **020060**

Customer Number: **38834**

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 C.F.R. §1.97(c)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

January 26, 2004

Sir:

The attention of the U.S. Patent and Trademark Office is hereby directed to the documents listed on the attached Form PTO-1449. One copy of each of these documents is attached.

These documents were cited in an European Search Report for a corresponding European application. A copy of the Search Report is also attached.

This Information Disclosure Statement is being submitted after the issuance of a first official action on the merits and expiration of the three month period following the filing date or the entry in the national stage for the above-captioned application, but prior to the issuance of either a Final Office Action, Notice of Allowance, or an action that otherwise closes prosecution in the application.

The undersigned hereby certifies:

☒ That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign


application not more than three months prior to the filing of the information disclosure statement and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in §1.56(c) more than three months prior to the filing of the information disclosure statement.

The above information is presented so that the Patent and Trademark Office may, in the first instance, determine any materiality thereof to the claimed invention. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references cited in the attached Form PTO-1449 is made of record therein and appear on the first page of any patent to issue therefrom.

The Commission is authorized to charge Deposit Account No. 50-2866 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

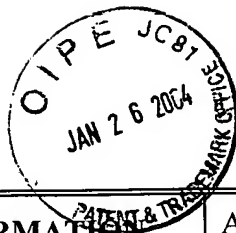
Respectfully submitted,

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Enclosures: Form PTO-1449 & 4 References  
European Search Report



<b>INFORMATION DISCLOSURE CITATION PTO-1449</b>	Atty. Docket No. <b>020060</b>	Serial No. <b>10/058,426</b>
	Applicant(s): <b>Daisuke KOMADA, et al.</b>	
	Filing Date: <b>January 30, 2002</b>	Group Art Unit: <b>1756</b>

### U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA	US 2001/004550'	Passemard	06/21/2001	438	618	
	AB	5,433,823	Cain	07/18/1995	156	662.1	
	AC						
	AD						
	AE						

### FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Translation (Yes or No)
	AF	WO 00/67304	11/09/2000	PCT	
	AG				
	AH				
	AI				
	AJ				

### OTHER DOCUMENTS'

	AK	P.H. YIH et al., <i>A Review of SiC Reactive Ion Etching in Fluorinated Plasmas</i> , Physica Status Solidi (b) vol. 202, pp. 605-642, (1997)
	AL	
Examiner		Date Considered